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[54] MOLECULAR FLUORINE (F_2) LASER WITH NARROW SPECTRAL LINewidth

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[51] Int. Cl. ⁷ H01S 3/098

[52] U.S. Cl. 372/19; 372/57; 372/20

[58] Field of Search 372/19, 100, 23, 372/20, 57, 29, 32

[56] References Cited

U.S. PATENT DOCUMENTS

3,868,592	2/1975	Yarborough et al.	331/94.5
4,393,505	7/1983	Fahlen	372/57
4,696,012	9/1987	Harshaw	372/99
4,829,536	5/1989	Kajiyama et al.	372/57
4,856,018	8/1989	Nozue et al.	372/98
4,975,919	12/1990	Amada et al.	372/33
4,977,563	12/1990	Nakatani et al.	372/32
5,081,635	1/1992	Wakabayashi et al.	372/57
5,095,492	3/1992	Sandstrom	372/102
5,150,370	9/1992	Furuya et al.	372/106
5,404,366	4/1995	Wakabayashi et al.	372/29
5,559,816	9/1996	Basting et al.	372/27
5,646,954	7/1997	Das et al.	372/55
5,684,822	11/1997	Partlo	372/95
5,761,236	6/1998	Kleinschmidt et al.	372/100
5,856,991	1/1999	Ershov	372/57
5,901,163	5/1999	Ershov	372/20
6,028,879	2/2000	Ershov	372/57

OTHER PUBLICATIONS

Optics and Laser Technology, vol. 11, No. 6, Dec. 1979, "CIF and F_2 ; two new ultra-violet laser systems," K. Hola, M. Diegelmann, H. Pummer, K.L. Kompa, 6 pgs.

Applied Physics B Photo-physics and Laser Chemistry, vol. B55, No. 1, Jul. 1992, "Influence of Cavity Configuration on the Pulse Energy of a High-Pressure Molecular Fluorine Laser," S.M. Hooker, A.M. Haxell, and C.E. Webb, 6 pgs.

Highlights Lambda-physik, Apr. 1993, "Excimer laser based microstructuring using mask projection techniques," U. Sarbach and H.J. Kahler, 4 pgs.

"High-power efficient vacuum ultraviolet F_2 laser excited by an electric discharge," V.N. Ishchenko, S.A. Kochubei, and A.M. Razhev, 3 pgs.

(List continued on next page.)

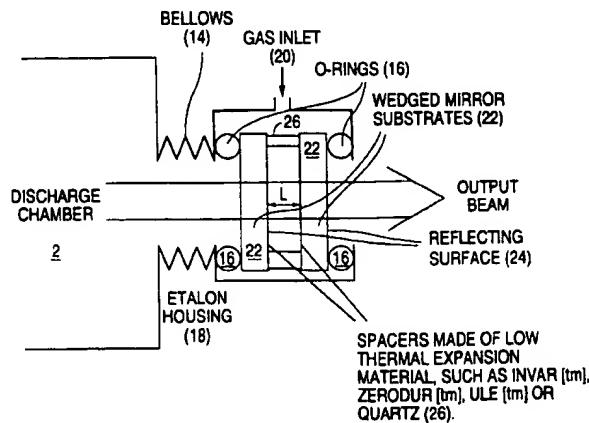
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[57] ABSTRACT

A molecular fluorine (F_2) laser is provided wherein the gas mixture comprises molecular fluorine for generating a spectral emission including two or three closely spaced lines around 157 nm. An etalon provides line selection such that the output beam only includes one of these lines. The etalon may also serve to outcouple the beam and/or narrow the selected line. Alternatively, a prism provides the line selection and the etalon narrows the selected line. The etalon may be a resonator reflector which also selects a line, while another element outcouples the beam. The etalon plates, preferably uncoated, comprise a material that is transparent at 157 nm, such as CaF_2 , MgF_2 , LiF_2 , BaF_2 , quartz and fluorine doped quartz. The etalon plates are separated by spacers comprising a material having a low thermal expansion constant, such as invar, zerodur®, ultra low expansion glass, and quartz. A gas such as helium or a solid such as CaF_2 that does not absorb radiation 157 nm fills the gap between the etalon plates, or the gap is evacuated. The gas mixture preferably further includes neon as a buffer gas. Another etalon may be used for line narrowing. One or more of a highly reflective mirror, a high finesse etalon or a prism with a highly reflective back surface may serve as a highly reflective resonator reflector. Any of one or more etalons, a prism, a brewster plate and a highly or partially reflective mirror may seal the laser discharge chamber.

33 Claims, 7 Drawing Sheets



OTHER PUBLICATIONS

- Conference on Lasers and Electro-optics*, 1990 Technical Digest Series, vol. 7, May 21-25, 1990, Anaheim, California, "Spectroscopic comparison between low and high pressure discharge pumped Xe atomic lasers," K. Komatsu, E. Matsui, S. Takahashi, Fumiko Kannari, M. Obara, 30 pgs.
- Applied Physics Letters*, vol. 56, Jun. 25, 1990, No. 26, "High specific output energy operation of a vacuum ultraviolet molecular fluorine laser excited at 66 MW/cm² by an electric discharge," Masayuki Kakehata, Etsu Hashimoto, Fumihiko Kannari and Minoru Obara, 6 pgs.
- Journal of Applied Physics*, vol. 50, Jun. 1979, No. 6, "Novel neutral atomic fluorine laser lines in a high-pressure mixture of F₂ and He," Shin Sumida, Minoru Obara, and Tomoo Fujioka, 10 pgs.
- IEEE Journal of Quantum Electronics*, Nov. 1991, vol. 27, No. 11, "Efficiency Characterization of Vacuum Ultraviolet Molecular Fluorine (F₂) Laser (157 nm) Excited by an Intense Electric Discharge," Masayuki Kakehata, Tatsuya Uematsu, Fumihiko Kannari, and Minoru Obara, 10 pgs.
- Journal of Modern Optics*, vol. 37, No. 4, Apr. 1990, "Amplification characteristics of a discharge excited F₂ laser," C. Skordoulis, E. Sarantopoulou, S. Spyrou and A.C. Cefalas, 12 pgs.
- Optics Communications*, vol. 55, No. 6, Oct. 15, 1985, "Gain Measurements at 157 nm in an F₂ Pulsed Discharge Molecular Laser," A.C. Cefalas, C. Skordoulis, M. Kompiatas and C.A. Nicolaides, 6 pgs.
- Applied Physics Letters*, vol. 54, Feb. 13, 1989, No. 7, "High-power discharge-pumped F₂ molecular laser," Kawakatsu Yamada, Kenzo Miyazaki, Toshifumi Hasama, and Takuzo Sato, 6 pgs.
- Leos '89*, Lasers and Electro-Optics Society Annual Meeting Conference Proceedings, Oct. 17-20, 1989, Orlando, Florida, "High Power Discharge Pumped F₂ Laser," K. Yamada, K. Miyazaki, T. Hasama, T. Sato, M. Kasamatsu, and Y. Mitsuhashi, 13 pgs.
- Journal of Applied Physics*, vol. 53, May 1982, No. 5, "Gain and saturation of the atomic fluorine laser," R. Sadighi-Bonabi, F.W. Lee, and C.B. Collins, 11 pgs.
- Conference on Lasers and Electro-Optics*, 1989 Technical Digest Series, vol. 11, May 24-28, 1989, Baltimore, Maryland, "Intense VUV-XUV generation from rare gas excimers," Wataru Sasaki, Kou Kurosawa, 23 pgs.
- Soviet Journal of Quantum Electronics*, 16(5) May 1986, "High-power efficient vacuum ultraviolet F₂ laser excited by an electric discharge," V.N. Ishchenko, S.A. Kochubei, and A.M. Kazhev, 9 pgs.
- Optics Communications*, vol. 28, No. 1, Jan. 1979, "Discharge pumped F₂ Laser at 1580 Å", H. Pummer, K. Hohla, M. Diegelmann and J.P. Reilly, 6 pgs.
- Gas Flow and Chemical Lasers*, SPIE No. 1397, Sep. 10-14, 1990, "Frequency up conversion of a discharge pumped molecular fluorine laser by stimulated Raman scattering in H₂," Masayuki Kakehata, Etsu Hashimoto, Fumihiko Kannari, and Minoru Obara, 16 pgs.
- The Journal of Chemical Physics*, vol. 69, Sep. 15, 1978, "An efficient, high power F₂ laser near 157 nm⁻¹," Joseph R. Woodworth and James K. Rice, 11 pgs.
- Vorhandlungen*, 3/1590, Phsyikertagung Munchen, 1990, Optimierung der VUV-Emission bei 157 nm (F₂-Linie) bei anladungs gepemten Excimerlasern, F. Voss, 2 pgs.
- Tasgungsband*, Vom, 24, Bis. Sep 26, 1991, Abstract: "Vakuum UV Molekullaser mit hoher Ausgangsleistung," 3 pgs.
- Applied Physics Letters*, vol. 51, No. 13, Sep. 28, 1997, "Theoretical evaluation of high-efficiency operation of discharge-pumped vacuum-ultraviolet F₂ lasers," Micko Ohwa and Minoru Obara, 6 pgs.
- Applied Optics VUV VI*, vol. 19, No. 23, Dec. 1, 1980, "Vacuum ultraviolet excimer lasers," M.H.R. Hutchinson, 9 pgs.
- Review of Scientific Instruments*, vol. 56, No. 5, Part 1, May 1985, "Simple, compact, high-repetition rate XeCl laser," E. Armandillo, G. Grasso, and G. Salvetti, 7 pgs.
- Applied Physics Letters*, vol. 31, No. 1, Jul. 1, 1977, "vuv emissions from mixtures of F₂ and the noble gasses A molecular F₁ laser at 1575 Å⁻¹," James K. Rice, A. Kay Hays, and Joseph R. Woodsworth, 5 pgs.
- Applied Physics Letters*, vol. 63, No. 4, Jul. 26, 1993, "Small-signal gain measurements in an electron beam pumped F₂ laser," H.M.J. Bassiaens, B.M.N.C. van Dam, P.J.M. Peters, and W. J. Witteman, 7 pgs.
- ZOS*, Akademie der Wissenschaften der DDR, Zentralinstitut für Optik und Wissenschaften der DDR, Oktober 1987, "Leistungaslarker atomarer Fluorlaser im roten Spektralbereich," Jürgen Lademann, Roland Kunig, Wadim Saldow, Rainer Weidauer, 12 pgs.
- Discharge-Pumped Excimer Laser Research in Japan, Apr. 1988, "Theoretical simulation of a discharge pumped F₂ excimer laser," T. Oematsu et al, Koio U.
- Science Report, Lambdaphysik*, No. 3, Nov. 1990, "Breakthrough in F₂Laser Technology," 4 pgs.
- Institut Fur Quantenoptik, Oct. 22, 1991, "Stimulated Raman scattering of a F₂-Laser in H₂," C. Momma, A. Tunnermann, F. Voß, C. Windolph and B. Wellegehausen, 8 pgs.
- Highlights, Lambdaphysik*, No. 33, Feb. 1992, "VUV Stokes and Anti-Stokes Raman Lines Derived from an F₂ Laser," C. Momma, A. Tunnermann, F. Voß, C. Windolph, and H. Wellegehausen, 5 pgs.
- Highlights, Lambdaphysik*, No. 43, Jan. 1994, "Photochemical modification of Fluorocarbon Resin to Generate Adhesive Properties," 6 pgs.
- Highlights Lambdaphysik*, No. 29, Jun. 1991, "VUV Spectroscopy by Frequency Tripling," 6 pgs.
- "Processing of PTFE with High Power VUV Laser Radiation," D. Basting, U. Sowada, F. Voß, P. Oesterlin, 3 pgs.
- Journal of Applied Physics*, vol. S1, No. 6, Mar. 1997, "Small signal gain measurements in a discharge-pumped F₂ laser," Tahei Kitamura, Yoshihiko Arild and Keisuke Maeda, Masayuki Takasaki, Kenshi Nakamura, Yoshiano Pujiwara and Shiro Horiguchi, 12 pgs.
- Journal of Applied Physics*, vol. 77, Jan. 1-16, 1995, "Long pulse electron beam pumped molecular F₂Laser," F.T.J.L. Lankhorst, H.M.J. Bastiacns, H. Betma, F.J.M. Peters, and W.J. Witteman, 8 pgs.
- Applied Physics*, Vol. B33, No. 4, Apr. 1984, "Intense Laser Generation from an Atomic-Fluorine," I.G. Koprinkov, K.V. Stamenov, and K.A. Stankov, 5 pgs.
- Journal of the Optical Society of America*, vol. 64, No. 4, Apr. 1974, "Modes of a laser resonator containing tilted birefringent plates," Arnold T., Bloom, 7 pgs.
- High Power Laser & Particle Beams*, vol. 6, No. 4, Series No. 24, Nov. 15, 1994.

SPIE—The International Society for Optical Engineering, Excimer Beam Applications, vol. 998, Sep. 6, 1988, Boston, Massachusetts, "Narrow-band KrF excimer laser—tunable and wavelength stabilized," Koich Wani, Yoshiro Ogata, Yoshiaki Watarai, Takuhiro Ono, Takeo Miyata, Reiji Sano, and Yasuaki Terui, 10 pgs.

Conference on Lasers and Electro-Optics, 1989 Technical Digest Series, vol. 11, Apr. 24 29, 1989, Baltimore, Maryland, "Line-narrowed industrial excimer laser for microlithography," R.K. Brimacombe, T.J. McKee, B.D. Mortimer, B. Norris, J. Reid, T.A. Znotins, 24 pgs.

Applied Optics, Aug. 1968, vol. 7, No. 8, "Theory of Multiplate Resonant Reflectors," J K. Watts, 3 pgs.

Applied Physics, 1978, "Nitrogen-Laser-Pumped Single-Mode Dye Laser," S. Saikan, 4 pgs.

Optics Communications, vol. 14, No. 1, May 1975, "Electronic Tuning of Dye Lasers by an Electrooptic Birefringent Fabry-Perot Etalon," Masakatsu Okada and Shoga Teiri, 7 pgs.

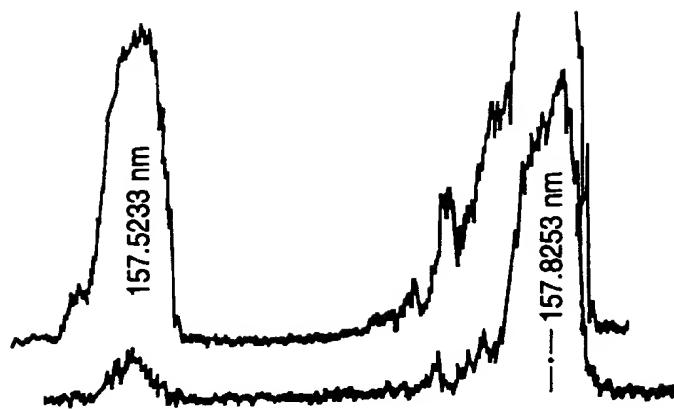


FIG. 1
(PRIOR ART)

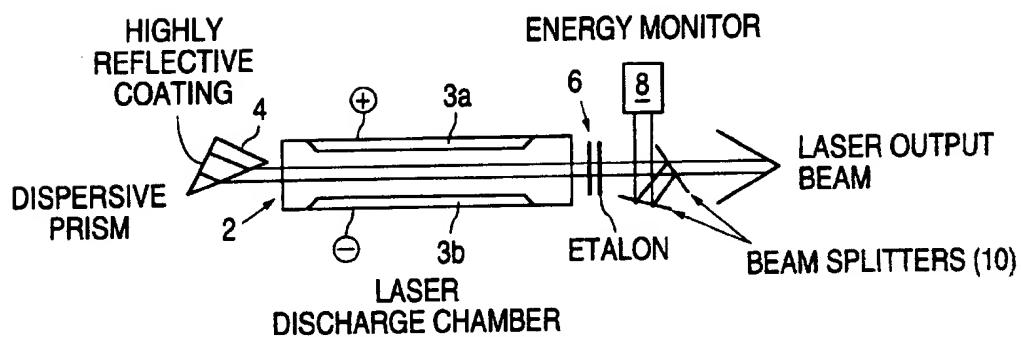


FIG. 2a

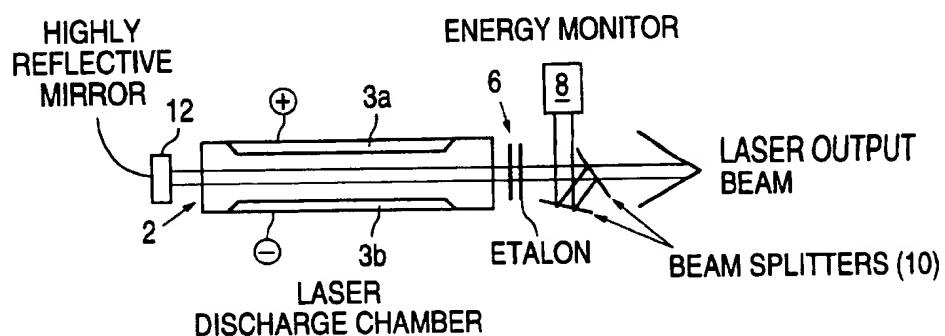
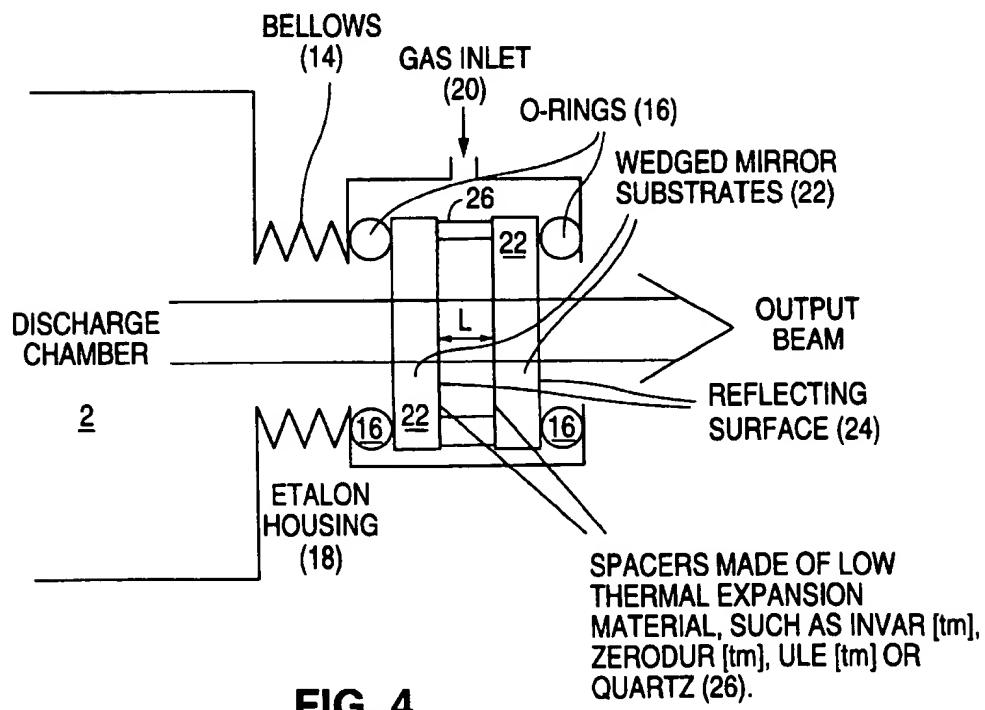
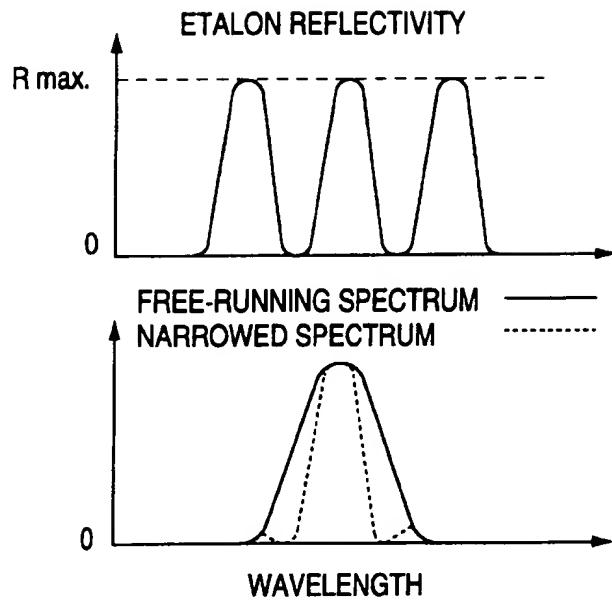
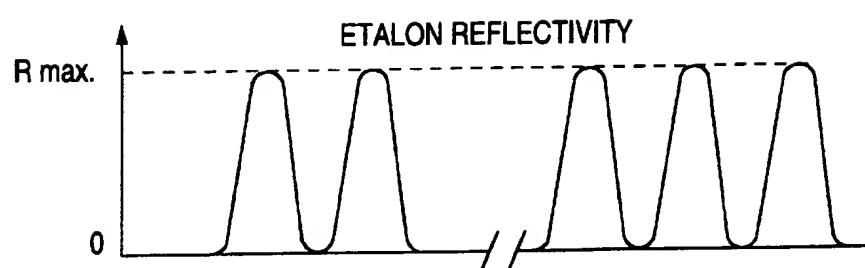
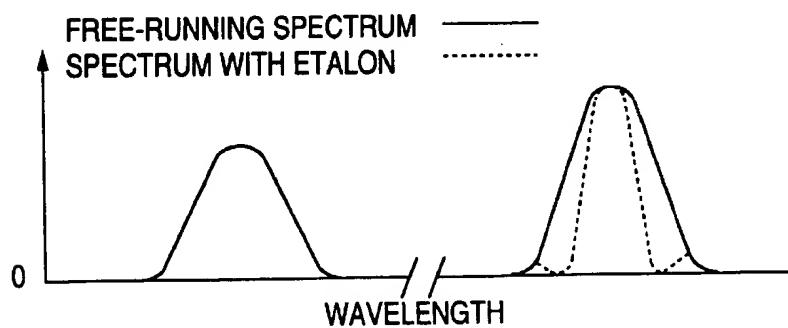
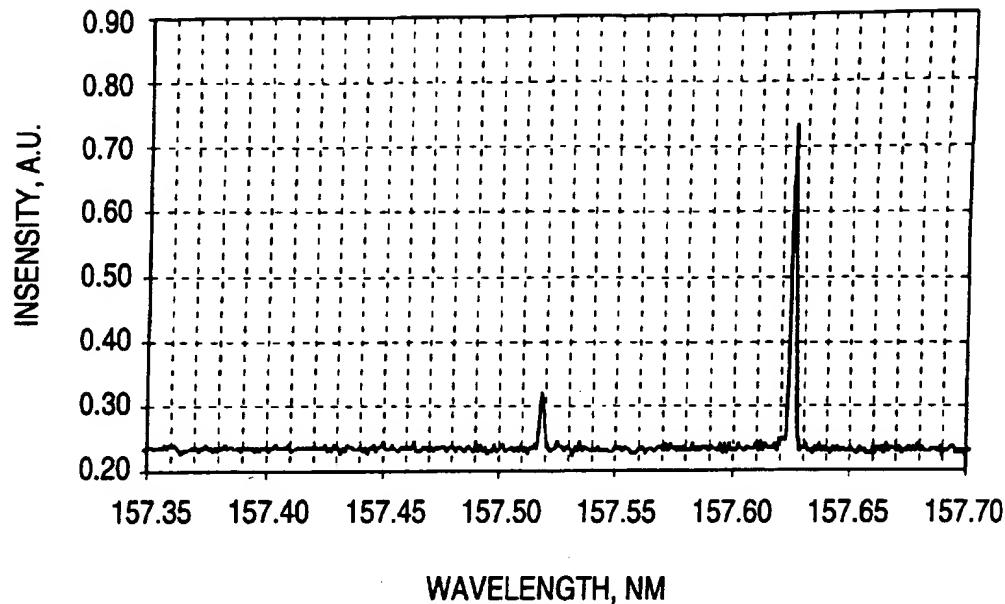
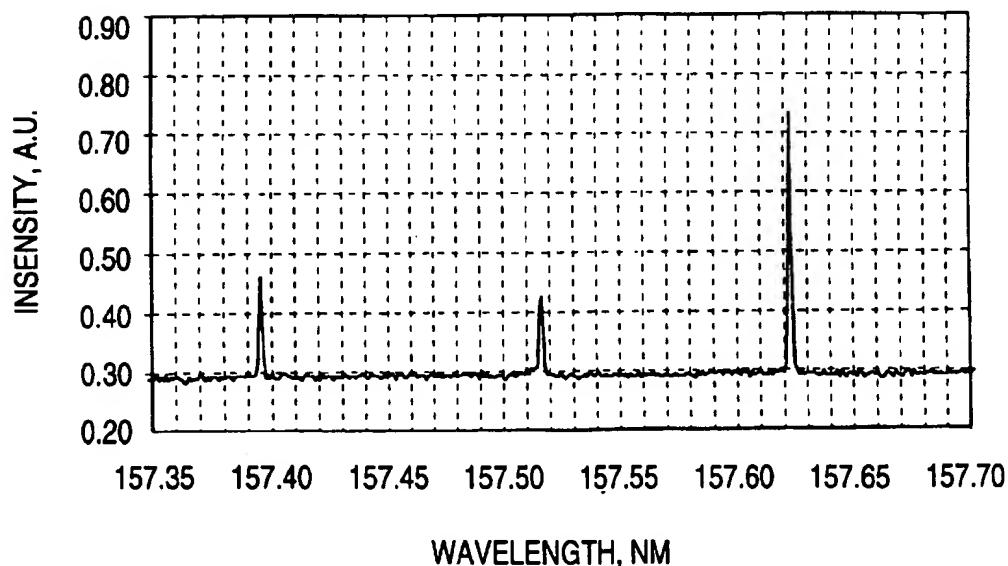


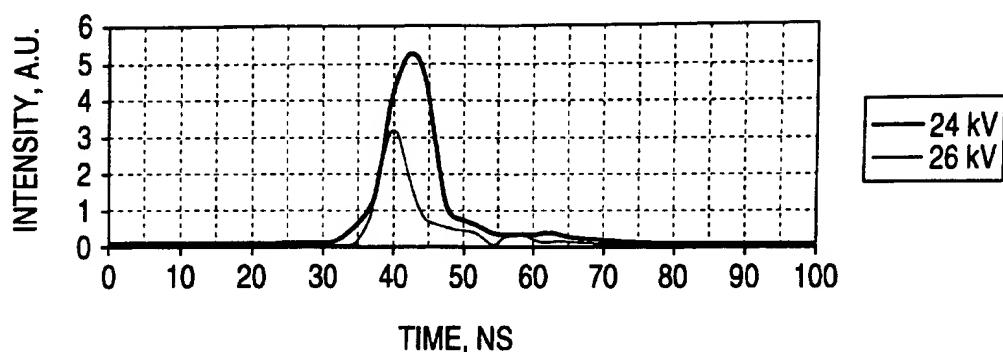
FIG. 2b



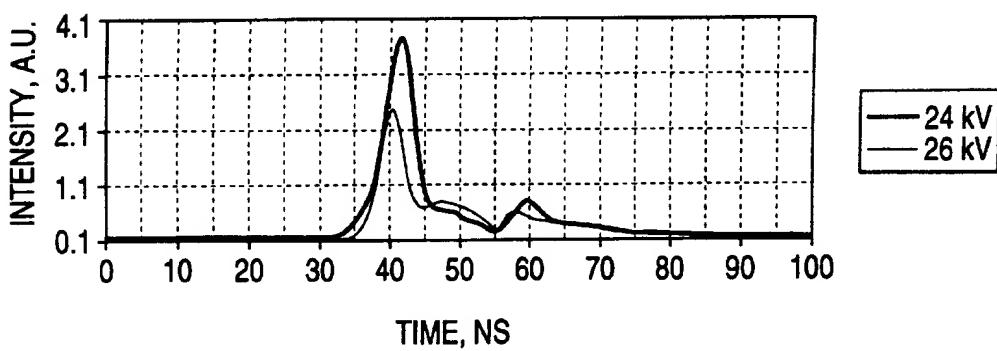
**FIG. 5a****FIG. 5b**

**FIG. 6a****FIG. 6b**

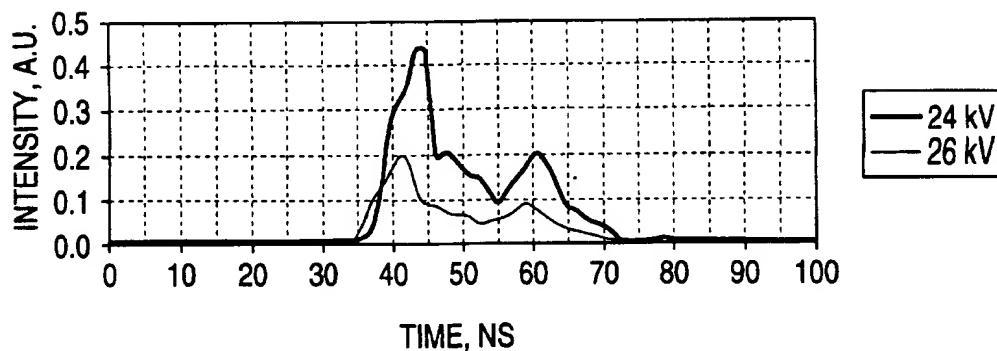
OSCILLOGRAM OF F2 LASER RADIATION

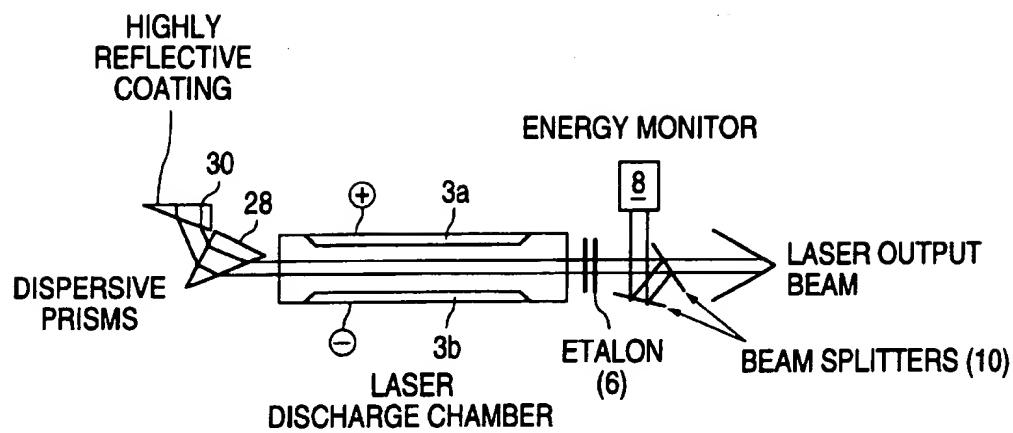
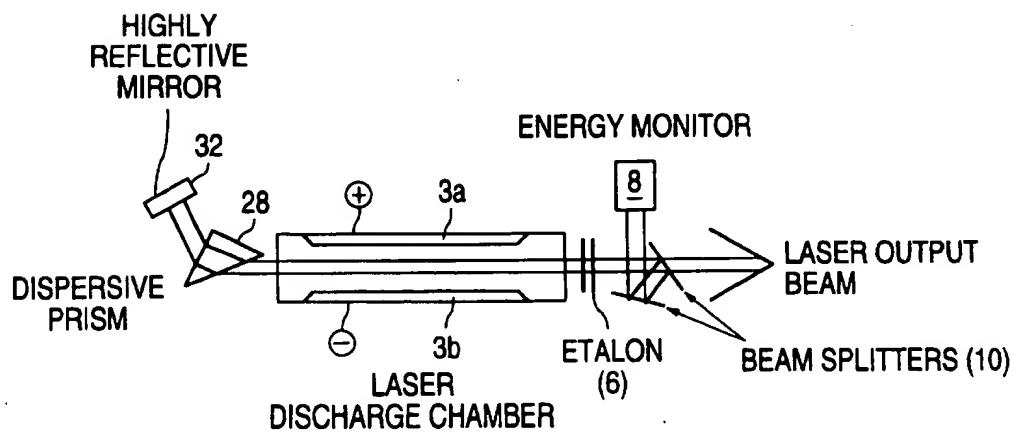
**FIG. 7a**

OSCILLOGRAM OF F2 LASER RADIATION

**FIG. 7b**

OSCILLOGRAM OF F2 LASER RADIATION

**FIG. 7c**

**FIG. 8a****FIG. 8b**

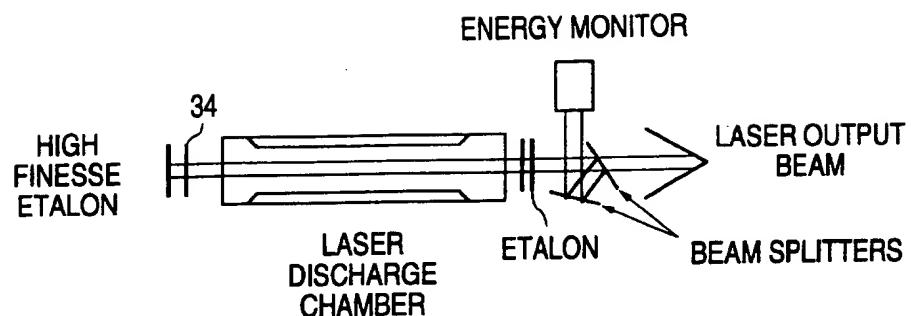


FIG. 9a

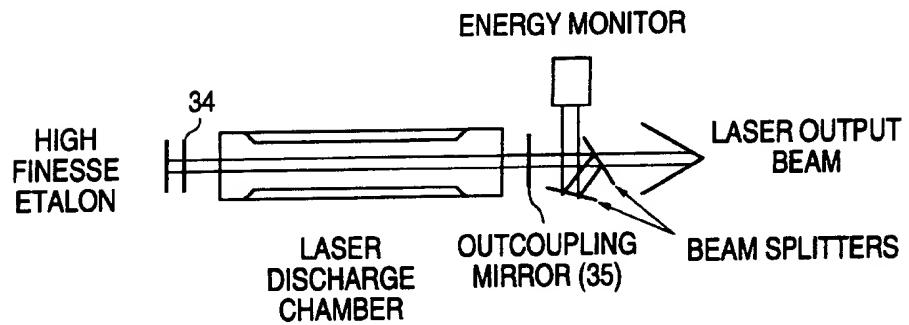


FIG. 9b

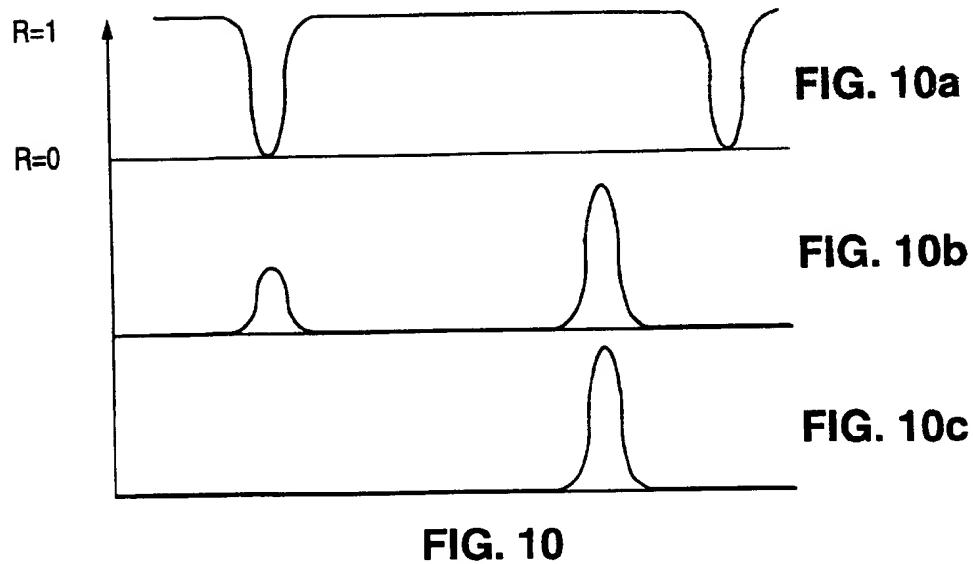


FIG. 10

1

MOLECULAR FLUORINE (F_2) LASER WITH NARROW SPECTRAL LINewidth

PRIORITY

This Application claims the benefit of U.S. Provisional Application Nos. 60/119,486, filed Feb. 10, 1999, and 60/120,218, filed Feb. 12, 1999, said applications being incorporated herein by reference.

BACKGROUND OF THE INVENTION

1. Field of the Invention

The invention relates to a molecular fluorine (F_2) laser, and particularly to an F_2 -laser having enhanced efficiency, line selection and line narrowing of the selected line.

2. Discussion of the Related Art

Semiconductor manufacturers are currently using deep ultraviolet (DUV) lithography tools based on KrF-excimer laser systems operating around 248 nm, to be followed by the next generation of ArF-excimer laser systems operating around 193 nm. Vacuum UV (VUV) is expected to use the F_2 -laser operating around 157 nm.

The emission of the F_2 -laser includes at least two characteristic lines around $\lambda_1=157.629$ nm and $\lambda_2=157.523$ nm. Each line has a natural linewidth of around 15 pm (0.015 nm). The intensity ratio between the two lines is $I(\lambda_1)/I(\lambda_2) \approx 7$. See V. N. Ishenko, S. A. Kochubel, and A. M. Razher, Sov. Journ. QE-16, 5 (1986). FIG. 1 illustrates the two above-described closely-spaced peaks of the F_2 -laser spontaneous emission spectrum.

Integrated circuit device technology has entered the sub-micron regime, thus necessitating very fine photolithographic techniques. Line narrowing and tuning is required in KrF- and ArF-excimer laser systems due to the breadth of their natural emission spectra (>100 pm). Narrowing of the linewidth is achieved most commonly through the use of a wavelength selector consisting of one or more prisms and a diffraction grating (Littrow configuration). However, for an F_2 -laser operating at a wavelength of approximately 157 nm, use of a reflective diffraction grating is unsatisfactory due to its low reflectivity and high oscillation threshold at this wavelength. The tunability of the F_2 -laser has been demonstrated using a prism inside the laser resonator. See M. Kakehata, E. Hashimoto, F. Kannari, M. Obara, U. Keio Proc. of CLEO-90, 106 (1990).

F_2 -lasers are also characterized by relatively high intracavity losses, due to absorption and scattering in gases and all optical elements, particularly in oxygen and water vapor which absorb strongly around 157 nm. The short wavelength (157 nm) is responsible for the high absorption and scattering losses of the F_2 -laser, whereas the KrF-excimer laser operating at 248 nm does not experience such losses. Therefore, the advisability of taking steps to optimize resonator efficiency is recognized in the present invention. In addition, output beam characteristics are more sensitive to temperature induced variations effecting the production of smaller structures lithographically at 157 nm, than those for longer wavelength lithography such as at 248 nm.

SUMMARY OF THE INVENTION

It is therefore an object of the invention to provide a F_2 -laser wherein one of the plural emission lines around 157 nm is efficiently selected.

It is a further object of the invention to provide the above F_2 -laser with efficient means for narrowing the selected line.

2

It is a further object of the invention to provide the F_2 -laser with a laser gas mixture selected to optimize laser output characteristics.

It is a further object of the invention to provide the F_2 -laser with a temperature stabilized output emission spectrum.

It is a further object of the invention to provide the F_2 -laser with an efficient optical resonator at 157 nm, preferably including a minimum number of optical elements and interfaces.

Therefore, the present invention provides a F_2 -laser wherein one of the plural lines of its output emission spectrum around 157 nm is selected, e.g., λ_1 (see above), for its use in lithography systems. The present invention also includes, and provides means for, narrowing the linewidth of the selected line. More specifically, the present invention uses a first etalon for selecting one of the plural lines around 157 nm of the F_2 -laser, and also functions to narrow the selected line. Alternatively, the first etalon performs line selection and another optical element such as a second etalon narrows the selected line. Also, alternatively, another element such as a second etalon, a prism, or a birefringent plate selects the line and the first etalon narrows the selected line.

When two etalons are used, one of the etalons is used for line selection and the other for narrowing of the selected line. Also, one of the etalons is used for output coupling and the other as a highly reflective resonator reflector.

The gas mixture pressure and components and their concentrations are selected for improved operation of the laser, including preferably using neon as a buffer gas, having a total pressure less than 5 bars and a having a fluorine concentration in a range between 0.05% and 0.20%. The number of optical interfaces, i.e., optical elements, in the resonator is reduced, and the materials and other properties comprising the optical elements and laser gas are selected to provide enhanced output beam characteristics.

The outcoupler etalon plates, preferably uncoated, comprise a material having a substantial transmissivity at 157 nm, such as CaF_2 , MgF_2 , LiF_2 , BaF_2 , SrF_2 , quartz and fluorine doped quartz. The etalon plates are separated by one, two or preferably three spacers comprising a material having a low thermal expansion constant, such as invar, zero-drift, ultra low expansion glass, or quartz. A gas, such as helium, another inert gas such as krypton, neon, argon or nitrogen, or generally a gas that does not absorb radiation strongly at 157 nm, or a solid such as one of those mentioned above for the plates fills the gap between the etalon plates, or the gap is evacuated.

The gas mixture in the discharge chamber preferably further includes neon as a primary buffer gas.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 shows an emission spectrum of an F_2 -laser without line selection or narrowing.

FIG. 2a shows a first preferred embodiment of a F_2 -laser in accord with the present invention.

FIG. 2b shows a second preferred embodiment of the present invention.

FIG. 3a illustrates the periodic wavelength dependence of the reflectivity function of an outcoupler etalon in accord with the present invention.

FIG. 3b illustrates an additional line-narrowing feature of the outcoupler etalon of FIG. 3a.

FIG. 4 shows an etalon as an outcoupler and a window of an F_2 -laser in accord with the present invention.

FIG. 5a shows the wavelength dependence of the reflectivity of an outcoupler etalon, in accord with the present invention, in the vicinity of the free-running F₂-laser emission lines λ_2 (left part) and λ_1 (right part) around 157 nm.

FIG. 5b shows the emission spectrum of the free-running F₂-laser without line selection or line narrowing (solid line) and with line selection and line narrowing (dashed line) performed by the outcoupler etalon of FIG. 5a.

FIG. 6a shows a free-running output emission spectrum of a F₂-laser with helium as a buffer gas.

FIG. 6b shows a free-running output emission spectrum of a F₂-laser with neon as a buffer gas.

FIG. 7a shows the temporal pulse shape of a F₂-laser having only helium as a buffer gas.

FIG. 7b shows the temporal pulse shape of a F₂-laser having helium and neon as buffer gases.

FIG. 7c shows the temporal pulse shape of a F₂-laser having mostly neon and only a very small concentration of helium as buffer gases.

FIG. 8a shows a third embodiment of a F₂-laser in accord with the present invention.

FIG. 8b shows a fourth embodiment of the present invention.

FIG. 9a shows a fifth embodiment of the present invention including a high finesse etalon.

FIG. 9b shows a sixth embodiment of the present invention including a high finesse etalon.

FIG. 10a shows the reflectivity spectrum of the high finesse etalon of either of FIGS. 9a or 9b in accord with the present invention.

FIG. 10b shows the free running output emission spectrum of an F₂-laser.

FIG. 10c shows the output emission spectrum of the F₂-laser whose free-running output emission spectrum is shown in FIG. 10b after line selection is performed by the high finesse etalon whose reflectivity spectrum is shown in FIG. 10a.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENT

FIGS. 2a and 2b show a first and a second preferred embodiments of a F₂-laser in accord with the present invention. The F₂-laser of the first embodiment includes a discharge chamber 2 filled with a laser gas including molecular fluorine and having main electrodes 3a and 3b coupled with a power supply circuit such that a voltage is applied across the electrodes 3a, 3b to create a pulsed discharge. UV-preionization of the electrical discharge laser is also provided and may be realized by means of an array of spark gaps or by another source of UV-radiation (surface, barrier or corona gas discharges), disposed in the vicinity of at least one of the solid electrodes of the main discharge of the laser. A preferred preionization unit is described in U.S. patent application Ser. No. 09/247,887 which is hereby incorporated by reference into this present application.

A dispersive prism 4 has a highly reflective coating at its back surface and serves as a highly reflective resonator reflector. An etalon 6 serves as an output coupler of the beam. The prism 4 may also serve to seal one end of the discharge chamber, while the etalon 6 also serves to seal the other end of the discharge chamber. Also, one of the etalon 6 and the prism 4 may serve to seal one end of the discharge chamber while the other end is sealed by a window. An energy monitor 8 is included in the first embodiment and

measures the energy of the output beam of the laser. Beam splitters 10 are also shown. One or more apertures (not shown) may also be inserted into the resonator to chop off sidebands of the dispersion spectrum of the prism 4 and/or of the superposition of the etalon 6 reflectivity maximum with the selected line of the F₂-laser. The aperture(s) can have dimensions which approximate the diameter of the laser beam (see U.S. patent application Ser. No. 09/130,277 filed Aug. 7, 1998). The apertures reduce the amount of amplified spontaneous emission generated in the gas discharge chamber 2. It is advantageous to chop out this otherwise parasitic emission because it does not generally possess the characteristics of desired laser oscillations. Therefore, if not excluded by an aperture, such parasitic emission can deteriorate the quality including the spectral purity and divergence of the output beam. Generally, any of the embodiments described herein may be varied by adding one or more apertures for excluding this parasitic emission.

Based partially on the energy measured using the energy monitor 8, the power supply voltage applied between the main electrodes 3a and 3b within the discharge chamber 2 and concentrations of constituents of the laser gas mixture are controlled to adjust characteristics of the output beam, including its energy. In the first preferred embodiment, line selection is achieved through the use of the dispersive prism 4. The prism is rotatable or tiltable to adjust the range of wavelengths it reflects within the acceptance angle of the resonator. The prism may be oriented to include only one of the multiple emission lines of the F₂-laser (see, e.g., FIGS. 1 and 6a-6b).

Due to the wavelength dependent nature of the refractive index of the material of the prism 4, light entering the prism 4 is refracted according to wavelength at various angles. Only a line having a wavelength within a particular range of wavelengths that exit the prism 4 within the acceptance angle of the resonator of the laser will later be outcoupled as the output laser beam. In other words, after retroreflecting from the highly reflecting surface at the back of the prism 4, lines of different wavelengths will enter the discharge chamber at different angles to the optical axis of the resonator. Lines having wavelengths within the range of wavelengths reflected within the acceptance angle of the resonator are selected, and all others are not selected or suppressed. The prism may be adjusted so that a desired center wavelength may be aligned parallel to the optical axis so that it suffers the least optical losses and, therefore, dominates the output. This center wavelength is at or near the center of the F₂-emission line it is desired to select.

Line narrowing is provided by the etalon 6 that also serves as an outcoupler. The etalon 6 has preferably a low finesse. The reflecting inner surfaces of the plates of the etalon 6 may exhibit, e.g., a reflectivity around 4-6%, such that a maximum reflectivity of the etalon may be from 16% to 24%. The reflectivity may, however, be somewhat increased/decreased to increase/decrease the overall gain of the F₂-laser, as desired.

An alternative embodiment may also be realized using one or more apertures with a dispersive element such as preferably a prism, and alternatively a grating. An aperture may be used for line selection when the prism is dispersing the emission of the F₂-laser. The selected line traverses the aperture, and the unselected line is blocked by the aperture. An etalon or prism may then be used for narrowing of the selected line.

Referring back to the first embodiment of FIG. 2a, wherein a single spectral line is selected by the prism 4 and

the selected line is narrowed by the optical etalon 6. FIGS. 3a and 3b illustrate how this line narrowing is achieved. The reflectivity function R of the etalon 6 versus the optical wavelength of incident light, in this case around 157 nm, is shown in FIG. 3a. The reflectivity function may be approximately represented by a sinusoidal function such as:

$$R(v) = 1 + \sin(2\pi v/v_0)$$

where v_0 is the free spectral range (FSR) of the etalon 6, $v_0 = \frac{c}{2nL}$ [cm⁻¹], where n is the refractive index of the material within the gap between the plates of the etalon 6 and L is the spacing of the etalon plates in centimeters. Those spectral components having frequencies close to the minimum of the etalon's 6 reflectivity R suffer the greatest losses in the resonator and are thus suppressed. Therefore, if the FSR of the etalon is approximately equal to, but is somewhat less than, the linewidth of the selected line of the free running laser, the output linewidth is narrowed. The FSR should not be much less than the free running linewidth, in order to prevent sidebands from developing in adjacent interference orders.

FIG. 3b shows a solid line representing the free-running linewidth of the selected line of the F₂-laser. The etalon reflectivity function of FIG. 3a is superimposed on the selected line. The resulting narrowed line is shown as a broken line in FIG. 3b. As noted above, if the FSR is too small then there will be significant overlap of the outer peaks of the reflectivity spectrum of FIG. 3a with the selected line. If "parasitic" sidebands are allowed to resonate, then beam quality may be deteriorated. When there is a dispersive element in the resonator, such as the prism 4 or another prism or prisms or a grating, the selected line may be narrowed further by reducing the width of the reflectivity maxima of the etalon 6, such that the etalon 6 does not suppress the sidebands, while apertures are placed within the resonator to chop off the sidebands, ultimately resulting in a very narrow, high quality output beam.

FIG. 4 shows an enlarged and more detailed view of the outcoupler etalon 6 of either of the first and second embodiments of FIGS. 2a and 2b. Alternatively, a solid etalon may be used, but the etalon shown in FIG. 4 having two plates separated by an air gap is preferred because the etalon reflectivity spectrum of the etalon of FIG. 4 may be adjusted by adjusting the pressure of the gas between the etalon plates (see below). FIG. 4 shows that the etalon 6 is preferably acting to both seal the discharge chamber 2 and as a window, in order to eliminate the lossy optical interfaces of an additional optical window sealing the chamber 2, and to reduce the overall size of the resonator setup. The etalon 6 may seal the chamber 2 via a bellows 14 and an o-ring 16, as shown in FIG. 4, in an exemplary embodiment.

The etalon 6 is shown encased within a housing 18. A gas inlet 20 is preferably provided for allowing one or more of gases such as helium (preferred), neon, krypton, argon, nitrogen, another inert gas or another gas that does not strongly absorb around 157 nm, to fill the housing 18 at a selected pressure. The housing is equipped with conventional means for measuring the pressure of the gas within it. Also, the gas inlet 20 may be used to pump the housing, including the gap between the plates 22 of the etalon 6, to a low pressure using a mechanical pump. Solid material such as CaF₂, MgF₂, LiF₂, BaF₂, SrF₂, quartz and fluorine doped quartz, or another solid material that does not absorb strongly around 157 nm may also fill the gap between the plates of the etalon 6. The reflecting interior surfaces of the plates 22 of the etalon 6 may be coated with a reflective film or may be left uncoated. The spacers 26 comprise a low

thermal expansion material such as invar™, zerodur, ultra low expansion (ULE™ glass) or quartz, or another material having a low constant of thermal expansion, such that the gap thickness L is least sensitive to temperature. This is advantageous because the reflectivity function of the etalon 6 depends on the gap spacing.

The following is an estimate of the preferred etalon gap thickness L. Since the linewidth of the free running F₂-laser is about 1 pm and the wavelength is approximately 157 nm, the FSR should be approximately 0.4 cm⁻¹. This means that the etalon spacing L should be 8.3 mm if the gap between the plates is filled with a solid material with a refractive index of around 1.5 (such as MgF₂, CaF₂, LiF₂, BaF₂, SrF₂, crystalline quartz or fluorine-doped quartz). Alternatively, and as discussed in more detail above, the etalon 6 can have its gap filled with an inert gas such as helium, in which case its thickness should be approximately 12.5 mm. Both of these spacings L are readily achievable. Use of the solid materials such as MgF₂, CaF₂, LiF₂, BaF₂, SrF₂ or crystalline or fluorine doped crystalline quartz for the plates of the etalon and/or to fill the gap is due in part to fact that these materials are mostly transparent to light at around a wavelength of 157 nm.

As alluded to above, an etalon design consideration is the desire for stability of the etalon frequency reflectivity maxima and minima with respect to the variations of ambient conditions, such as the temperature. For example, MgF₂ has a linear expansion coefficient of $13.7 \times 10^{-6} \text{ K}^{-1}$ along the c-axis, and a temperature index coefficient of $1.47 \times 10^{-6} \text{ K}^{-1}$ for an ordinary beam. This means that in order to maintain the centering of the spectral line with respect to a maximum of the reflectivity function R(v), e.g., within 10% of FSR, one should stabilize the temperature to within 0.06 K. If CaF₂ is used, then the stability should be within 0.05 K.

The present invention provides this stability by using low thermal expansion materials for its spacers. It also does so by providing the outcoupler etalon 6 of the first or second embodiments of FIGS. 2a or 2b, respectively, with two plates separated by a gap within the housing described above preferably filled with an inert gas, such as one or a combination of the gases mentioned above, wherein the pressure of the gas is controlled to control the index of refraction of the gas and thus the center wavelength of the aligned peak of the reflectivity function of the etalon. For inert gases such as nitrogen, the refractive index changes by approximately 300 ppm per 1 bar of pressure. Therefore, with the spacing between reflecting surfaces L=12.5 mm, frequency control within 10% of the FSR requires pressure control within 2 mbars of resolution. As discussed, the first reason to use helium in the pressure-tuned etalon 6, or alternatively nitrogen, argon or other inert gases or vacuum is because air is not transparent at the 157 nm wavelengths of interest, primarily due to the presence of oxygen, water vapor and carbon dioxide in the air, each of which strongly absorbs around 157 nm.

Additionally, the internal surfaces of the outcoupler etalon 6 may either be coated with partially reflective coatings, or may be uncoated. In the latter case which is preferred, the reflectivity of each surface is approximately 4 to 6% which results in a maximum reflectivity of the etalon from 16% to 24%. Similar considerations apply to the solid etalon.

The second embodiment of FIG. 2b is similar to the first embodiment of FIG. 2a, and differs in that the prism 4 of FIG. 2a is replaced in FIG. 2b by a highly reflective mirror 12. The highly reflective mirror 12 may seal one end of the discharge chamber and/or the etalon 6 may seal the other end of the discharge chamber. In the second embodiment, the

etalon 6 provides the line selection function, obviating the prism 4 of the first embodiment of FIG. 2a. An advantage of the second embodiment over the first embodiment is simplicity, fewer elements in the resonator and fewer optical interfaces for the beam to traverse which leads to reduced optical losses and increased lifetime. However, suppression of the second line may be less efficient in the second embodiment than in the first embodiment.

In the second embodiment, the etalon 6 is used for both line selection and simultaneously, for narrowing the selected single line, in a fashion similar to that described above with respect to the first embodiment. The line selection is achieved by adjusting the FSR and the wavelength of the maximum reflectivity of the etalon in such a way that the reflectivity at the desired wavelength is maximized, and the reflectivity at the wavelength of other non-selected lines is at its minimum. This line selection is described in greater detail below. The etalon 6 also outcouples the beam as it did in the first embodiment.

The FSR of the etalon 6 of the first and second embodiments, or more generally that of any gas-filled etalon used with the F₂-laser of the present invention, such as the etalon 6 of FIGS. 8a, 8b or 9a or the etalon 34 of FIGS. 9a-9b (below), is adjustable in the following manner. The pressure of the gas filling the etalon housing 18 (see FIG. 4), and particularly the gas between the plates 22 of the etalon 6, may be varied to adjust the index of refraction of the gas. Alternatively, the spacing L between the plates 22 can be varied, e.g., using piezo elements as etalon spacers 26. By either of these methods, the FSR can be adjusted because the FSR depends on both the index of refraction of the gas and the spacing L between the plates 22. By adjusting the FSR of the etalon 6, line selection may be precisely performed by aligning a maximum in the reflectivity spectrum of the etalon 6 with the desired line to be selected, and by contemporaneously aligning a minimum of the reflectivity spectrum of the etalon 6 with the unselected line of the free-running F₂-laser.

FIGS. 5a and 5b illustrate schematically how the line narrowing is performed by the etalon 6. As discussed quantitatively below, the FSR of the etalon 6 is adjusted by either changing its gap spacing, or by varying pressure of the gas in the gap, as has been described above. The requirements to the pressure resolution derived above, also apply to this case. The advantage of this configuration is simplicity, since no prism is required for line selection. However, the system may be less efficient at suppressing the unwanted lines, leading to residual emission at those wavelengths.

The reflectivity spectrum of the etalon 6 in the vicinity of the free-running F₂-laser emission lines λ_2 (left part) and λ_1 (right part) around 157 nm is shown in FIG. 5a. Preferably the pressure of the gas filling the gap of the etalon 6 is varied to align reflectivity maxima and minima with λ_1 and λ_2 , respectively. Alternatively, the gap spacing may be varied or both the pressure and gap spacing may be varied to produce the same effect. FIG. 5b shows λ_2 (left part) and λ_1 (right part) of the free running F₂-laser (solid line), and the output emission spectrum of the F₂-laser with line selection (λ_1) and narrowing of the selected line (dashed line). That is, the dashed line of FIG. 5b represents the reflectivity spectrum of FIG. 5a of the etalon 6 superimposed over the solid line of FIG. 5b, which is the output emission spectrum of the free running F₂-laser.

In addition to molecular fluorine, the gas mixture within the discharge chamber of the F₂-laser of the present invention further includes one or more other gases including at least one buffer gas. FIGS. 6a and 6b show spectra of the free-running F₂-laser with helium and neon as a buffer gas, respectively.

FIG. 6a shows the free-running F₂-laser spectrum around 157 nm with helium as the buffer gas. Two lines are observed. FIG. 6b shows the free-running F₂-laser spectrum around 157 nm with neon as the buffer gas. In this case, three lines are observed. The corresponding lines around 157.62 nm and 157.52 nm of the spectrum of FIG. 6b are notably narrower than those of the spectrum of FIG. 6a. This is because the F₂-laser which emitted the spectrum of FIG. 6b exhibited a longer pulse duration due to the presence of the neon buffer gas, than did the F₂-laser which emitted the spectrum of FIG. 6a having helium as a buffer gas.

In any embodiment of the F₂-laser of the present invention, the longer the pulse duration, the narrower the spectral linewidth which is achievable. On each roundtrip of the laser beam inside the resonator, there occurs a spectral filtering of the beam. After each reflection from the etalon output coupler 6, the intensity spectrum of reflected beam $I^{(j+1)}(\nu)$ is the product of reflectivity function of the etalon R(ν) and incident spectrum $I^{(j)}(\nu)$:

$$I^{(j+1)}(\nu) = R(\nu) I^{(j)}(\nu),$$

where j is the number of the round-trip. If, for example, the reflectivity function can be approximated by a Gaussian function, the width of the beam spectrum decreases as an inverse square root of the number of roundtrips:

$$\Delta\nu \sim j^{-1/2}.$$

The present invention provides means of increasing the length of the pulse of the molecular fluorine laser by utilizing neon as a buffer gas. FIGS. 7a, 7b and 7c show the temporal pulse shape with the gas mixtures shown in Table 1:

TABLE 1

Figure	Neon	Helium	Fluorine
7a	0	99.87%	0.13%
7b	48.4%	51.5%	0.13%
7c	96.8%	3.1%	0.13%

An increase in the concentration of neon in the gas mixture of the F₂-laser results in an increased pulse length from roughly 8 nsec (for 0% neon) to 25 nsec (for 96.8% neon).

Total Pressure and Fluorine Concentration Considerations

The gas mixtures are optimized with respect to pulse energy (gain) and pulse energy stability. Higher pressure and higher fluorine concentration each achieve a higher energy result, but also produce a higher pulse energy fluctuation. The preferred arrangement thus balances these considerations. Thus, a total pressure of approximately 5 bar and a fluorine concentration in the range 0.05% to 0.2% is preferred.

In the preferred embodiment employing neon as the buffer gas, three lines are present in the free-running spectrum. The following conditions should be satisfied:

$$\begin{aligned} m v_0 &= v_1; \\ (k+\frac{1}{2})v_0 &= v_2; \\ (j+\frac{1}{2})v_0 &= v_3, \end{aligned}$$

where m, j, k are integers, v₀ is the free spectral range of the etalon in the optical frequency domain, v₁ is the optical

frequency of the line to be selected, and v_2 and v_3 are optical frequencies of spectral lines to be suppressed. In the case where only two lines present, such as if helium is used as the buffer gas, this set of equations is reduced to two equations:

$$m v_0 = v_1;$$

$$(k+\frac{1}{2})v_0 = v_2;$$

where v_1 , the optical frequency of the line to be selected.

FIGS. 8a and 8b show third and fourth embodiments, respectively, of the present invention. In order to increase the wavelength separation effect, one may use multiple (two or more) prisms 28,30 as shown in FIG. 8a. The second prism 30 would have a high reflectivity coating at its back surface. Also, use of a separate highly reflective mirror 32 instead of the highly reflective coating on the back surface of the prism 30 is shown in FIG. 8b. Such separate highly reflective mirror 32 can be used in combination with multiple prisms as well. An advantage of the separate mirror 32 is that it can be manufactured more readily than the prism 30. At the same time, use of the separate mirror 32 increases the number of optical surfaces that the beam traverses, thus increasing both optical losses and wavelength dispersion. Consequently, a decision on the number of prisms and whether to use a separate mirror is dependent on the total magnitude of the dispersion needed for achieving reliable selection of the single line. As noted above, one or more apertures may be inserted into the resonator of either of the systems of FIGS. 8a & 8b to chop off sidebands of the dispersion spectrum of the prisms 28,30 and/or of the superposition of the etalon 6 reflectivity maximum with the selected line of the F₂-laser.

FIGS. 9a and 9b show fifth and sixth embodiments, respectively, of the present invention. In the fifth embodiment of FIG. 9a, a high finesse etalon 34 replaces the prism 4 of the first embodiment of FIG. 2a. In the sixth embodiment of FIG. 9b, the high finesse etalon 34 is again used, and an outcoupling mirror 35 replaces the outcoupling etalon 6 of the fifth embodiment of FIG. 9a. Generally, any of the embodiments described herein may be altered to include the high finesse etalon shown in FIGS. 9a and 9b.

In either of the fifth or sixth embodiments, line selection is achieved through the use of the etalon 34, which preferably has a relatively high finesse. The etalon 34 of FIGS. 9a and 9b works in reflection mode and may also serve to replace the high reflectivity surface of previously described embodiments, i.e., the high reflectivity back surface of the prism 4 in the first embodiment or the prism 30 in the third embodiment, the high reflectivity mirror 12 of the second embodiment or the high reflectivity mirror 32 of the third embodiment. Further, the etalon 34 may replace the entire prism 12, 30 or prism 28 and reflector 28, due to its line selection property coupled with its high reflectivity property.

The reflectivity of the etalon 34 versus the optical frequency v of the laser beam is shown in FIG. 10a. It is represented by the function

$$R(v) \sim F \sin^2(\pi v/v_0)/(1 + F \sin^2(\pi v/v_0)),$$

where $F=4R/(1-R)^2$ is the finesse factor of the etalon 34, v_0 is the free spectral range (FSR) of the etalon, $v_0=\frac{1}{2} nL$ [cm⁻¹], where n is the refractive index of the etalon gap material and L is the spacing of the etalon in centimeters. The finesse factor relates to the finesse F as $F=\pi\sqrt{F/2}$. Spectral components having frequencies close to the minimum of the reflectivity function of the etalon 34 suffer the greatest losses in the resonator and, therefore, are suppressed. If the finesse of the etalon 34 is sufficiently high, then any light having a frequency outside of the narrow

spectral area corresponding to the condition $v=k v_0$, where K =integer, will be almost entirely reflected by the etalon 34, which exhibits a reflectivity of nearly unity at those frequencies, as shown in FIG. 10a. Therefore, except for these narrow areas of minimum reflection at $v=k v_0$, the etalon 34 acts simply as a highly reflective surface. Preferably, the etalon 34 is configured to suppress undesirable spectral lines by setting a minimum or minimums of reflectivity of the etalon 34 at the center(s) of such line(s). An etalon 34 according to either of the fifth or sixth embodiments may be either a solid-state etalon, an evacuated etalon or an inert gas filled etalon as described above, wherein the inert gas may again be one or a combination of any of helium, argon, neon, krypton, nitrogen, or another gas that does not absorb light strongly around 157 nm. Also, the gap between the plates of the etalon 34 may include solid material such as CaF₂, MgF₂, LiF₂, BaF₂, SrF₂, quartz or fluorine doped quartz, or another solid material that does not strongly absorb light around 157 nm.

FIG. 10a-10c illustrate the line selection feature of the high finesse etalon 34 of FIGS. 9a and 9b. FIG. 10a shows the wavelength dependence of the reflectivity of the high finesse etalon 34. FIG. 10b shows the emission spectrum of the free-running F₂-laser. The resulting output emission of the F₂-laser having the high finesse etalon 34 in its resonator setup is shown in FIG. 10c. As can be observed from FIGS. 10a-10c, one of two lines is selected as output of the F₂-laser, as desired.

Wavefront curvature of the beam may also be compensated by using a cylindrical lens within the resonator (see U.S. patent application Ser. No. 09/073,070 filed Apr. 29, 1998). The etalons 6 and 34 of the present invention are generally sensitive to the wavefront curvature of the beam. Thus, one or more cylindrical lenses placed in the resonator can provide a more collimated beam at the etalon(s) 6,34. Moreover, wavefront curvature compensation can be achieved via one or more curved resonator mirrors.

Other variations are possible in furthering the goals and objects of the present invention. For example, any of the prism 4 of FIGS. 2a, the highly reflective mirror 12 of FIGS. 2b, the etalon 6 in any embodiment, the prism 28 or the prism 30 of FIG. 8a, the prism 28 or the highly reflecting surface 32 of FIG. 8b, and the high finesse etalon 34 of FIGS. 9a and 9b may seal off the laser discharge chamber 2. This advantageously reduces the number of optical interfaces the beam has to traverse, and thus reduces optical losses. In particular, an extra laser window or windows is not needed after one or more of the optical elements just mentioned is substituted therefor. When an etalon 6,34 is used to seal the discharge chamber, it may be advantageous to raise the pressure of the gas within the etalon 6,34 to near the pressure of the gas mixture, to prevent distortion of the etalon 6,34 due to the pressure difference, but only if the etalon may still perform its line selection and/or narrowing function.

In this regard, the scope of the present invention is meant to be that set forth in the claims that follow, and equivalents thereof, and is not limited to any of the specific embodiments described above.

What is claimed is:

1. An F₂-laser, comprising:
a discharge chamber filled with a gas mixture including molecular fluorine generating a spectral emission including a plurality of closely spaced lines in a wavelength range between 157 nm and 158 nm, said plurality of closely-spaced lines including a primary line centered around a wavelength of 157.62 nm and a secondary line centered around a wavelength of 157.52 nm;

11

a pair of electrodes coupled with a power supply circuit producing a pulsed discharge to energize said molecular fluorine; and

a resonator including a prism and a first etalon, said prism being arranged at a particular orientation for dispersing the plurality of closely spaced lines including the primary and secondary lines such that only the primary line centered around 157.62 nm remains within an acceptance angle of the resonator and any other line(s) including the secondary line centered around 157.52 nm are dispersed outside of the acceptance angle of the resonator such that only the primary line at 157.62 nm is amplified among said plurality of closely-spaced lines, said first etalon being arranged for maximum reflectivity of a central portion of the primary line around 157.62 nm and for relatively low reflectivity of outer portions of the primary line to substantially suppress said outer portions, thereby narrowing the primary line such that said F₂-laser emits a single wavelength laser beam having a narrow spectral linewidth that is less than the linewidth of the 157.62 line of a free-running F₂ laser to provide a narrow band VUV laser beam.

2. An F₂-laser as in claim 1, said prism having a highly reflective back surface for reflecting a laser beam as a highly reflective resonator reflector.

3. An F₂-laser as in one of claims 1-2, said first etalon being part of the resonator further for outcoupling a laser beam.

4. An F₂-laser as in claim 3, said prism for sealing one end of the discharge chamber.

5. An F₂-laser as in one of claims 1-2, said prism for sealing one end of the discharge chamber.

6. A F₂-laser as in any of claims 1 or 2, wherein said etalon comprises CaF₂ plates.

7. A F₂-laser as in any of claims 1 or 8, wherein said prism comprises CaF₂.

8. An F₂-laser as in claim 1, said first etalon including two plates with one of the two plates having a highly reflective surface for reflecting a laser beam as a highly reflective resonator reflector.

9. An F₂-laser as in one of claims 1 or 8, wherein said gas mixture further includes a buffer gas including neon.

10. An F₂-laser as in claim 9, wherein the concentration of said neon within said gas mixture is above 90%.

11. An F₂-laser as in claim 9, wherein an interior surfaces of each of said two plates of said first etalon is uncoated.

12. An F₂-laser as in one of claims 1 or 8, wherein said first etalon includes two plates separated by a gap and said first etalon is in a housing filled with an inert gas.

13. An F₂-laser as in one of claims 1 or 8, further comprising an aperture within the resonator along the optical path of the beam.

14. An F₂-laser as in claim 13, said aperture having a dimension approximately equal to, yet less than, a beam dimension.

15. An F₂-laser as in claim 13, said aperture for selecting one of said plurality of closely-spaced lines, said aperture being arranged for permitting a maximum intensity of the selected line to propagate within the acceptance angle of the resonator and for blocking any unselected lines.

12

16. An F₂-laser as in claim 15, further comprising a second etalon for narrowing the selected line, said second etalon being arranged for maximum reflectivity of a central portion of the selected line and for relatively low reflectivity of outer portions of the selected line to suppress said outer portions.

17. An F₂-laser as in claim 16, said second etalon being part of the resonator further for outcoupling a laser beam.

18. An F₂-laser as in claim 16, wherein said second etalon includes two plates with one of the two plates having a highly reflective inner surface for reflecting a laser beam as a highly reflective resonator reflector.

19. An F₂-laser as in claim 18, wherein said second etalon is a high finesse etalon.

20. An F₂-laser as in one of claims 1 or 8, wherein said first etalon is a low finesse etalon.

21. An F₂-laser as in one of claims 1 or 8, wherein said first etalon has an adjustable free spectral range.

22. An F₂-laser as in claim 21, wherein the free spectral range of said first etalon is one of pressure-tuned and piezo-tuned.

23. A F₂-laser as in claim 8, wherein said etalon comprises CaF₂ plates.

24. An F₂-laser as in claim 1, further comprising a second prism for further narrowing of the selected line, said second prism being arranged for refracting a first portion of the selected line within the acceptance angle of the resonator and for refracting a second portion of the selected line outside of the acceptance angle of the resonator to suppress the second portion.

25. An F₂-laser as in claim 1, wherein said first etalon seals one end of said discharge chamber.

26. An F₂-laser as in claim 25, wherein said first etalon includes two plates separated by a gap and said first etalon is in a housing filled with an inert gas.

27. An F₂-laser as in claim 26, said gas within said housing having a pressure approximately equal to the pressure of said gas mixture.

28. An F₂-laser as in one of claims 26, wherein said first etalon includes two plates separated by one or more spacers comprising one or more of invar, zerodur, ultra low expansion glass, and quartz.

29. An F₂-laser as in claim 28, wherein said schott glass is zerodur™ schott glass, and said ultra low expansion glass is ULE™ ultra low expansion glass.

30. An F₂-laser as in one of claims 26, wherein said two plates of said first etalon comprise one or more of CaF₂, MgF₂, LiF₂, BaF₂, SrF₂, quartz and fluorine doped quartz.

31. An F₂-laser as in claim 1, wherein said first etalon includes two plates separated by a gap filled with a material selected from the group of materials consisting of CaF₂, MgF₂, LiF₂, BaF₂, SrF₂, quartz and fluorine doped quartz.

32. An F₂-laser as in claim 1, wherein said first etalon includes two plates separated by a gap and said first etalon is in an evacuated housing.

33. An F₂-laser as in claim 1, wherein the pressure of said gas mixture is substantially less than 5 bars.

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